

PJQ44611AP-AU

60V P-Channel Enhancement Mode MOSFET

Voltage **-60 V** **Current** **-13 A**

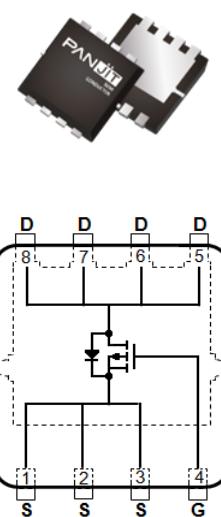
Features

- $R_{DS(ON)}$, $V_{GS} @ -10V$, $I_D @ -6A < 84m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ -4.5V$, $I_D @ -3A < 117m\Omega$
- 100% UIS tested
- Reliable and Rugged
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams

DFN3333-8L



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^(Note 3)	I_D	-13	A
		-9	
Pulsed Drain Current ^(Note 1)	I_{DM}	-24	W
Power Dissipation	P_D	31	
		15	A
Continuous Drain Current ^(Note 4)	I_D	-3.9	
		-3.2	W
Power Dissipation	P_D	2.5	
		1.8	mJ
Single Pulse Avalanche Current ^(Note 5)	I_{AS}	-7	
Single Pulse Avalanche Energy ^(Note 5)	E_{AS}	20	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~175	°C
Thermal Resistance ^(Note 4)	Junction to Case	$R_{\theta JC}$	4.8 °C/W
	Junction to Ambient	$R_{\theta JA}$	60

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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-60	-	-	V
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-1.7	-2.5	
Drain-Source On-State Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-6\text{A}$	-	67.4	84	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-3\text{A}$	-	90	117	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-60\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
Dynamic ^(Note 6)						
Total Gate Charge	Q_g	$V_{\text{DS}}=-30\text{V}, I_{\text{D}}=-6\text{A}, V_{\text{GS}}=-10\text{V}$	-	18	24	nC
Gate-Source Charge	Q_{gs}		-	3	-	
Gate-Drain Charge	Q_{gd}		-	3.5	-	
Input Capacitance	C_{iss}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	844	1200	pF
Output Capacitance	C_{oss}		-	52	95	
Reverse Transfer Capacitance	C_{rss}		-	35	65	
Gate resistance	R_g	$f=1\text{MHz}$	-	14	-	Ω
Turn-On Delay Time	$t_{\text{d(on)}}$	$V_{\text{DS}}=-30\text{V}, I_{\text{D}}=-6\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{G}}=3\Omega$ <small>(Note 2)</small>	-	4.9	-	ns
Turn-On Rise Time	t_r		-	3.1	-	
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	27	-	
Turn-Off Fall Time	t_f		-	12	-	
Drain-Source Diode						
Diode Forward Current	I_s	$T_c=25^\circ\text{C}$	-	-	-13	A
Pulsed Diode Forward Current	I_{SM}		-	-	-24	
Diode Forward Voltage	V_{SD}	$I_s=-6\text{A}, V_{\text{GS}}=0\text{V}$	-	-0.85	-1.3	V
Reverse Recovery Time	T_{rr}	$V_{\text{DD}}=-30\text{V}, V_{\text{GS}}=0\text{V}, I_s=-6\text{A}, dI_s/dt=100\text{A}/\text{us}$	-	11	-	ns
Reverse Recovery Charge	Q_{rr}		-	6	-	

NOTES :

1. Pulse width $<300\text{us}$, Duty cycle $<2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4. R_{JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
5. E_{AS} is calculated based on the condition of $L=1\text{mH}$, $I_{\text{AS}}=-6.3\text{A}$, $V_{\text{DD}}=-30\text{V}$, $V_{\text{GS}}=-10\text{V}$. 100% test at $L=0.5\text{mH}$, $I_{\text{AS}}=-7\text{A}$ in production.
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

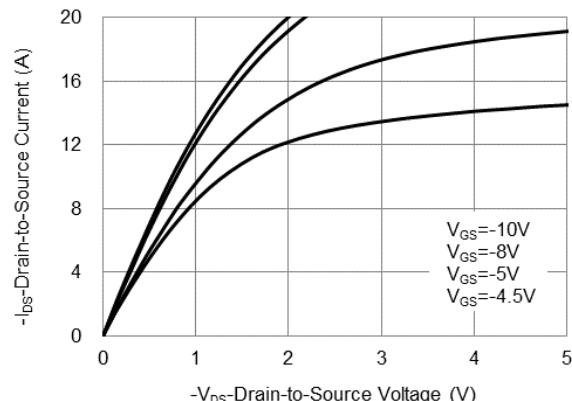


Fig.1 On-Region Characteristics

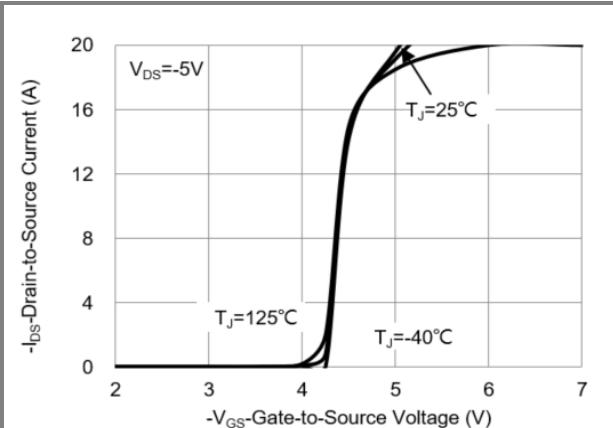


Fig.2 Transfer Characteristics

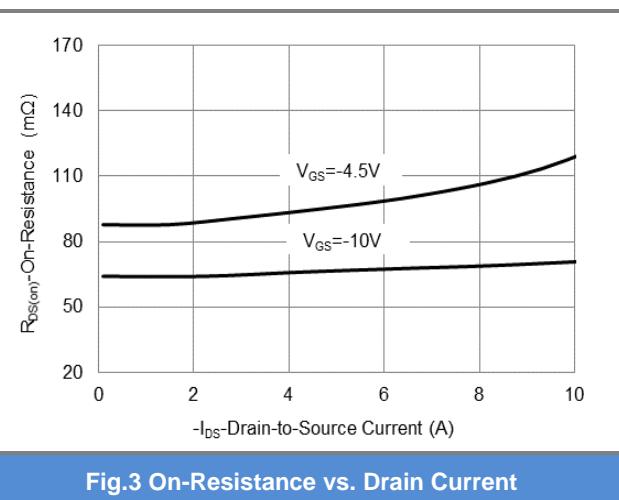


Fig.3 On-Resistance vs. Drain Current

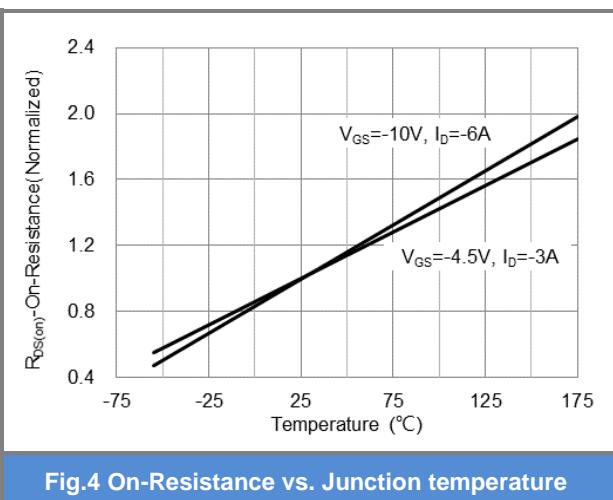


Fig.4 On-Resistance vs. Junction temperature

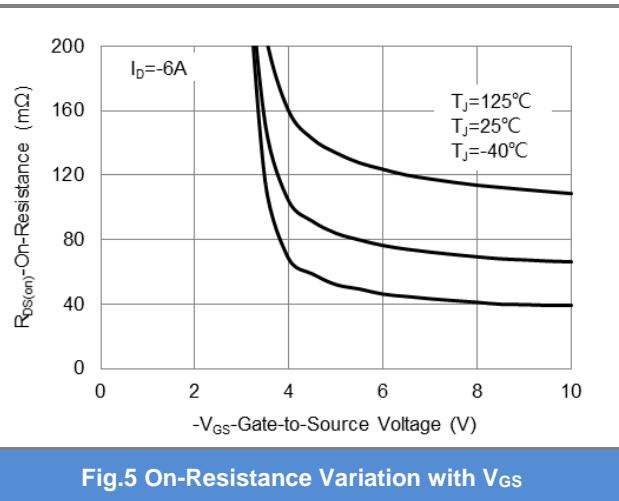


Fig.5 On-Resistance Variation with VGS

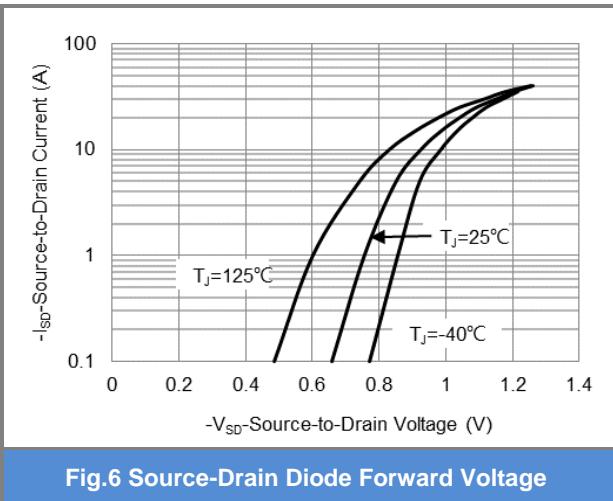


Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

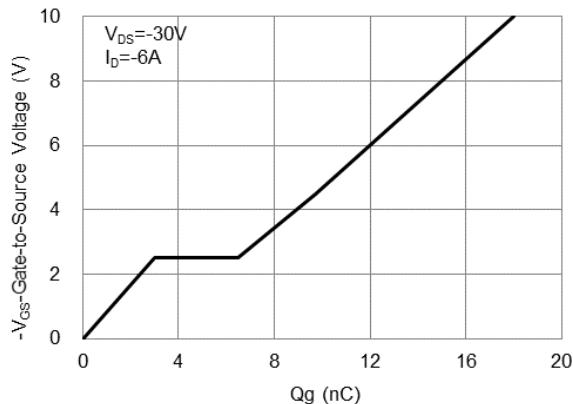


Fig.7 Gate-Charge Characteristics

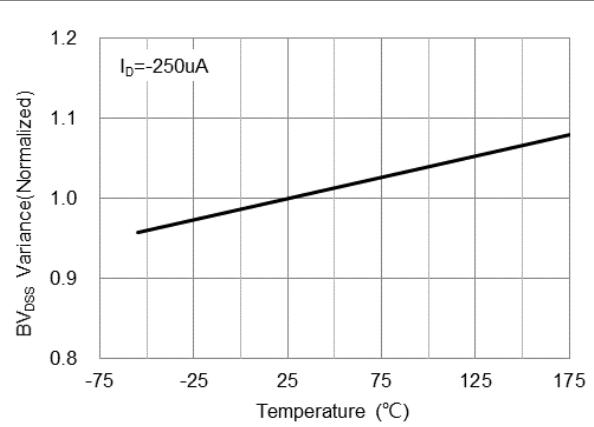


Fig.8 Breakdown Voltage Variation vs. Temperature

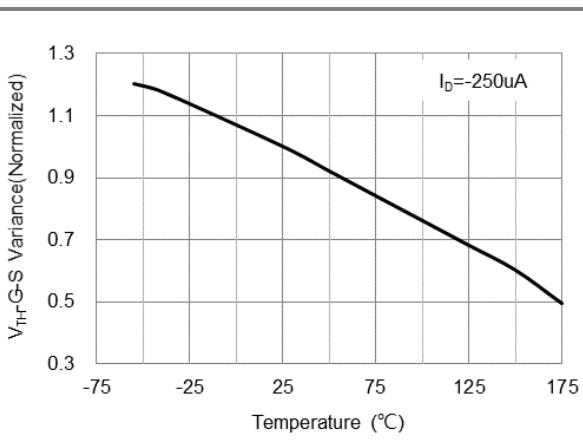


Fig.9 Threshold Voltage Variation with Temperature

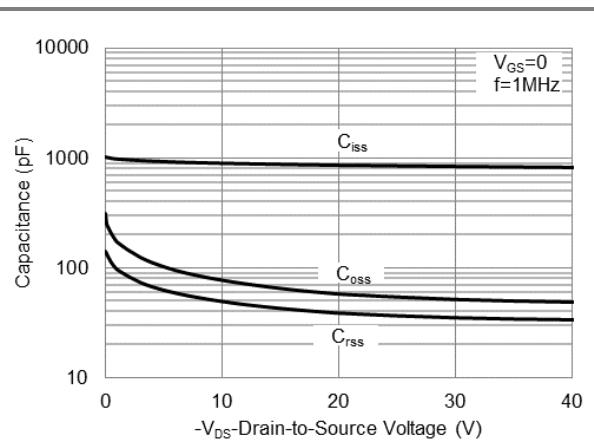


Fig.10 Capacitance vs. Drain-Source Voltage

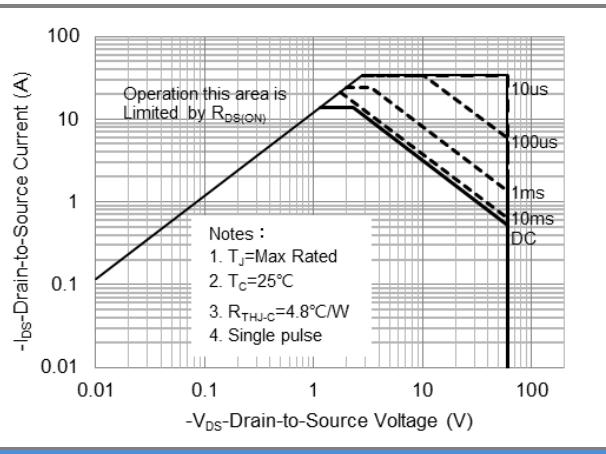


Fig.11 Maximum Safe Operating Area

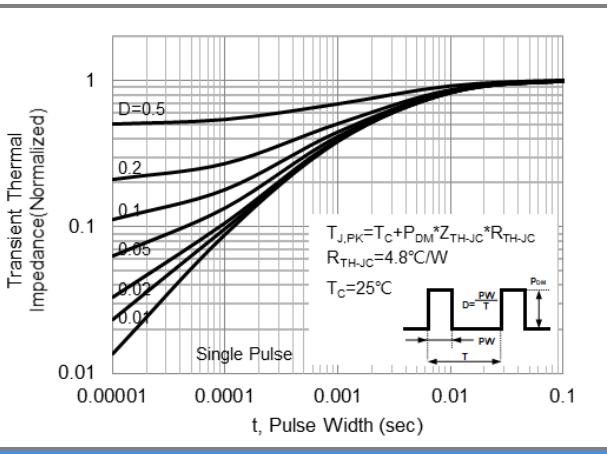


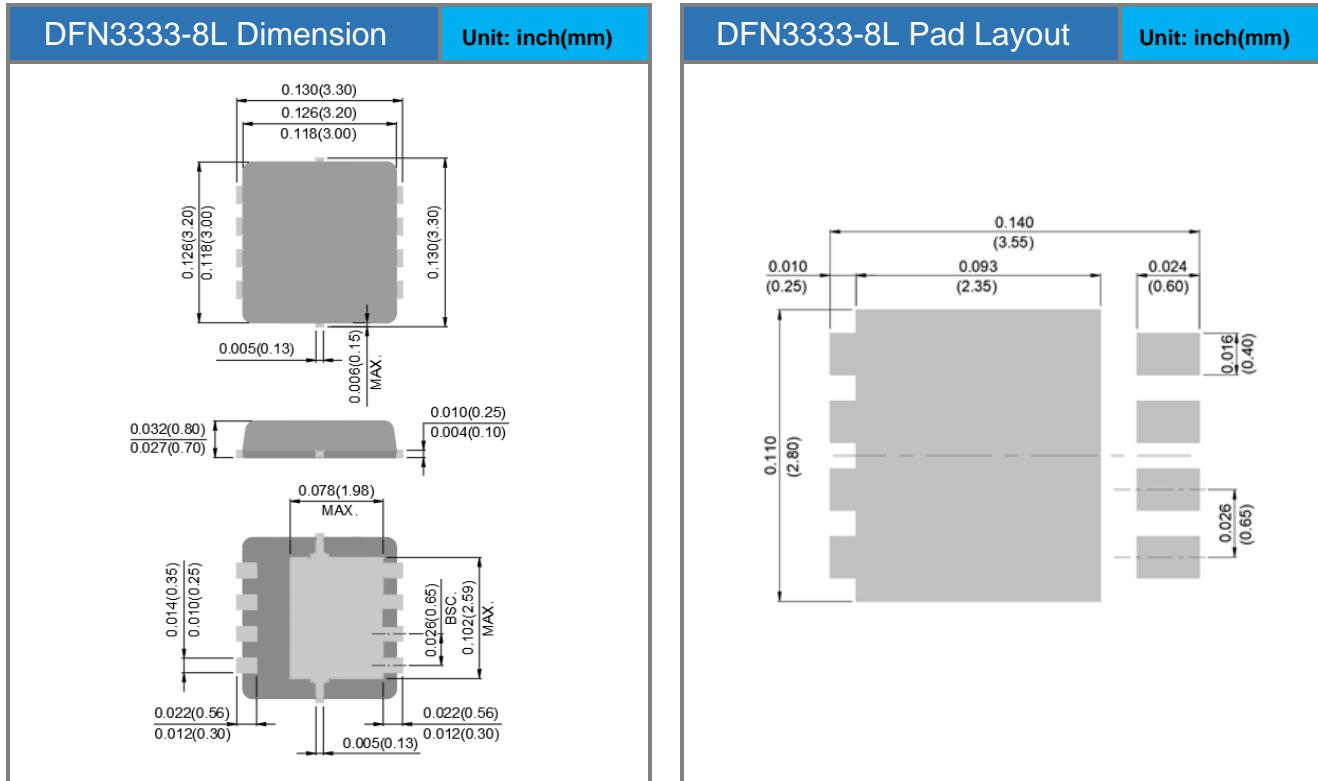
Fig.12 Normalized Transient Thermal Impedance

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Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ44611AP-AU	DFN3333-8L	5K pcs / 13" reel	44611A

Packaging Information & Mounting Pad Layout



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